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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Hwang, et al.

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Serial No.: 10/092,456

Group Art Unit: 2818

Confirmation No.: 1212

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Filed: March 6, 2002

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Filed: March 6, 2002

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For: ETCHING METHODS FOR A MAGNETIC MEMORY CELL STACK

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Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

The Applicants, and the Attorney who signs below on the basis of the information supplied by the inventor and the information in his file, submit herewith patents, publications, or other information of which they are aware, which may be material to the examination of this application and in respect of which there may be a duty to disclose in accordance with 37 CFR § 1.56.

While the information submitted in this Supplemental Information Disclosure Statement may be material pursuant to 37 CFR § 1.56, it is not intended to constitute an admission that any patent, publication, or other information referred to therein is prior art for this invention unless specifically designated as such.

In accordance with 37 CFR § 1.97, this Supplemental Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possibly material information as defined under 37 CFR § 1.56(a) exists.

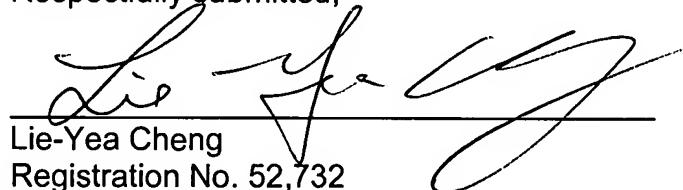
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The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

Applicants certify that all references submitted with this disclosure were cited in a communication from a foreign patent office dated October 23, 2003, which communication is enclosed, not more than three months prior to the filing of this Supplemental Information Disclosure Statement.

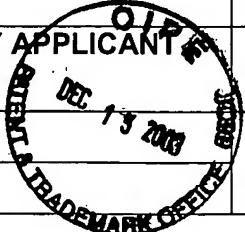
If the sum of \$180.00 is due under 37 CFR § 1.17(p) pursuant to § 1.97, the Commissioner is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to the Deposit Account No.: 20-0782/AMAT/6437/LYC.

Respectfully submitted,



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U.S. Department of Commerce, Patent and Trademark Office (PTO Form 1449 modified)		Docket No. AMAT/6437/ETCH/METAL/JB1	Serial No. 10/092,456
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Applicant Hwang, et al.	Confirmation No. 1212
(Use several sheets if necessary)		Filing Date March 6, 2002	Group 2818
	Examiner Dung Anh Le		

**U.S. Patent Documents**

*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
	A1						
	A2						
	A3						
	A4						
	A5						

Foreign Patent Documents

*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
							YES	NO
	B1						<input type="checkbox"/>	<input type="checkbox"/>
	B2						<input type="checkbox"/>	<input type="checkbox"/>
	B3						<input type="checkbox"/>	<input type="checkbox"/>
	B4						<input type="checkbox"/>	<input type="checkbox"/>
	B5						<input type="checkbox"/>	<input type="checkbox"/>

OTHER ART

*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.
	C1	Jung, K.B., et al., "Long term stability of dry etched magnetoresistive random access memory elements", <i>Journal of Vacuum Science and Technology:Part A</i> ; American Institute of Physics, New York, U.S., Vol. 18, No. 1, January 2000 (2000-01), pp. 268-272, XP001145970, ISSN: 0734-2101.
	C2	van Delft, F.C.M.J.M., et al., "The etch mechanisms of magnetic materials in an HCl plasma", Fusion Technology and Plasmas Session of the Twelfth International Vacuum Congress (IVC-12) and Eighth International Conference on Solid Surfaces (ICSS-8), The Hague, Netherlands, 12-16 Oct. 1992, Vol. 200, No. 3, pp. 366-370, XP008022404, <i>Journal of Nuclear Materials</i> , May 1993, Netherlands, ISSN: 0022-3115.
	C3	Cho, H. et al., "Inductively coupled plasma etching of CoFeB, CoZr, CoSm and FeMn thin films in interhalogen mixtures", <i>Materials Science and Engineering B (Solid-State Materials for Advanced Technology)</i> , 15 June 1999, Elsevier, Switzerland, Vol. B60, No. 2, pp. 107-111, XP004175032, ISSN: 0921-5107.

Examiner

Date Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.